

Microsemi
POWER PRODUCTS GROUP

APT2X101D100J 1000V 95A
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DUAL DIE ISOTOP® PACKAGE

ULTRAFAST SOFT RECOVERY RECTIFIER DIODE

PRODUCT APPLICATIONS

- Anti-Parallel Diode
 - Switchmode Power Supply
 - Inverters
- Free Wheeling Diode
 - Motor Controllers
 - Converters
- Snubber Diode
- Uninterruptible Power Supply (UPS)
- Induction Heating
- High Speed Rectifiers

PRODUCT FEATURES

- Ultrafast Recovery Times
- Soft Recovery Characteristics
- Popular SOT-227 Package
- Low Forward Voltage
- High Blocking Voltage
- Low Leakage Current

PRODUCT BENEFITS

- Low Losses
- Low Noise Switching
- Cooler Operation
- Higher Reliability Systems
- Increased System Power Density

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT2X101_100D100J	UNIT
V_R	Maximum D.C. Reverse Voltage	1000	Volts
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		
V_{RWM}	Maximum Working Peak Reverse Voltage		
$I_F(AV)$	Maximum Average Forward Current ($T_C = 77^\circ\text{C}$, Duty Cycle = 0.5)	95	Amps
$I_F(RMS)$	RMS Forward Current (Square wave, 50% duty)	131	
I_{FSM}	Non-Repetitive Forward Surge Current ($T_J = 45^\circ\text{C}$, 8.3ms)	1000	
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to 175	$^\circ\text{C}$
T_L	Lead Temperature for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol		MIN	TYP	MAX	UNIT
V_F	Forward Voltage	$I_F = 100\text{A}$		1.9	Volts
		$I_F = 200\text{A}$		2.2	
		$I_F = 100\text{A}, T_J = 125^\circ\text{C}$		1.7	
I_{RM}	Maximum Reverse Leakage Current	$V_R = V_R \text{ Rated}$		250	μA
		$V_R = V_R \text{ Rated}, T_J = 125^\circ\text{C}$		500	
C_T	Junction Capacitance, $V_R = 200\text{V}$		110		pF

DYNAMIC CHARACTERISTICS

APT2X101_100D100J

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t_{rr}	Reverse Recovery Time	$I_F = 1A$, $di_F/dt = -100A/\mu s$, $V_R = 30V$, $T_J = 25^\circ C$	-	43		ns
t_{rr}	Reverse Recovery Time	$I_F = 100A$, $di_F/dt = -200A/\mu s$ $V_R = 667V$, $T_C = 25^\circ C$	-	300		
Q_{rr}	Reverse Recovery Charge		-	800		nC
I_{RRM}	Maximum Reverse Recovery Current		-	7	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 100A$, $di_F/dt = -200A/\mu s$ $V_R = 667V$, $T_C = 125^\circ C$	-	360		ns
Q_{rr}	Reverse Recovery Charge		-	4050		nC
I_{RRM}	Maximum Reverse Recovery Current		-	19	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 100A$, $di_F/dt = -1000A/\mu s$ $V_R = 667V$, $T_C = 125^\circ C$	-	170		ns
Q_{rr}	Reverse Recovery Charge		-	7400		nC
I_{RRM}	Maximum Reverse Recovery Current		-	70		Amps

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			.41	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance			20	
W_T	Package Weight		1.03		oz
			29.2		g
Torque	Maximum Terminal & Mounting Torque			10	lb•in
				1.1	N•m

Microsemi Reserves the right to change, without notice, the specifications and information contained herein.

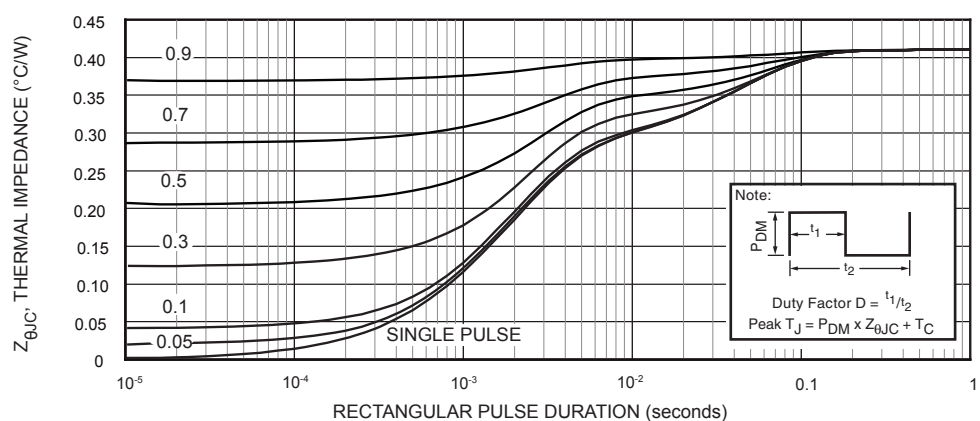


FIGURE 1. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

TYPICAL PERFORMANCE CURVES

APT2X101_100D100J

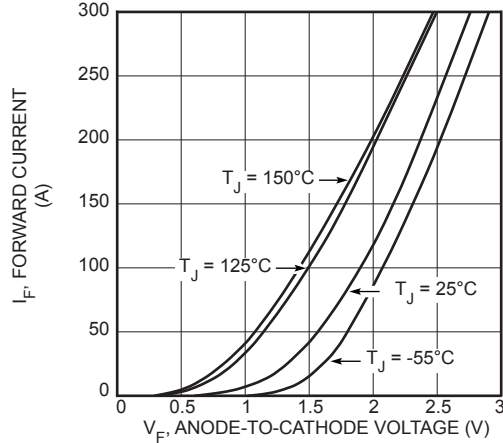


Figure 2. Forward Current vs. Forward Voltage

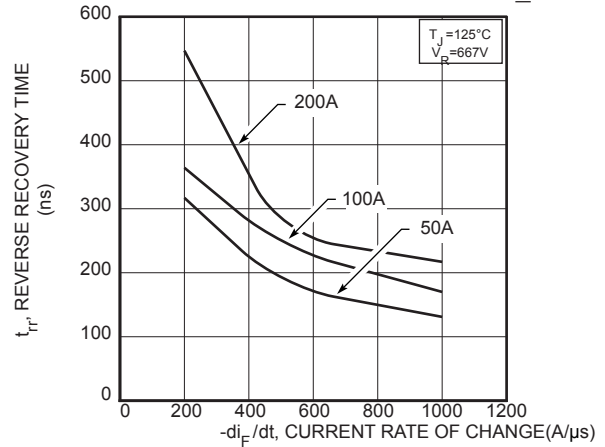


Figure 3. Reverse Recovery Time vs. Current Rate of Change

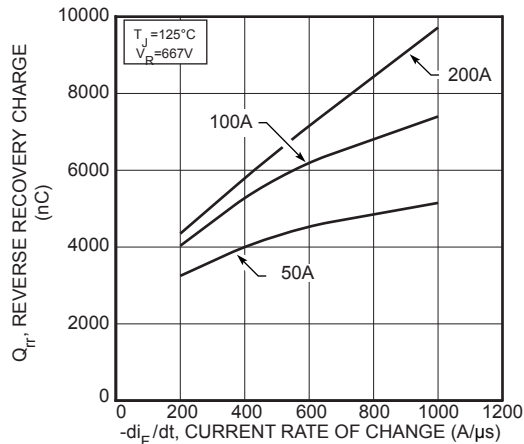


Figure 4. Reverse Recovery Charge vs. Current Rate of Change

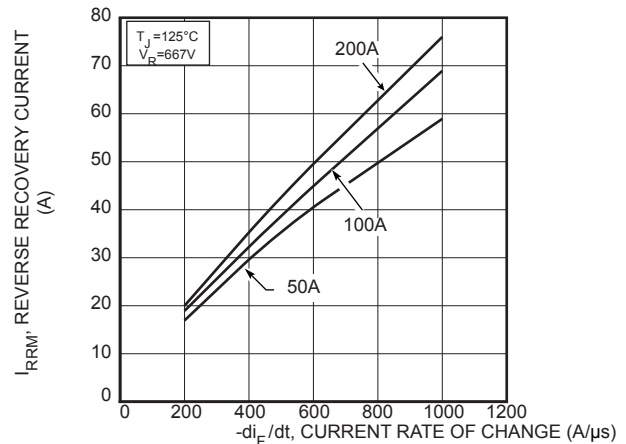


Figure 5. Reverse Recovery Current vs. Current Rate of Change

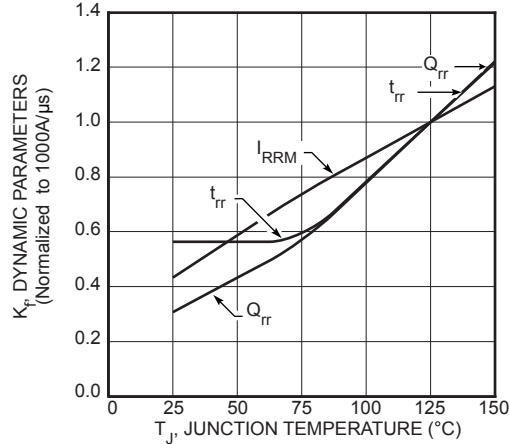


Figure 6. Dynamic Parameters vs. Junction Temperature

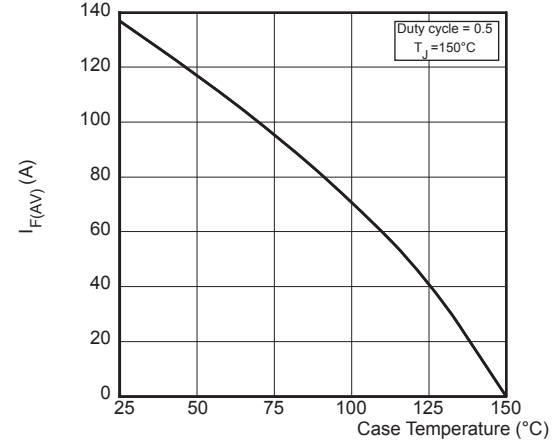


Figure 7. Maximum Average Forward Current vs. Case Temperature

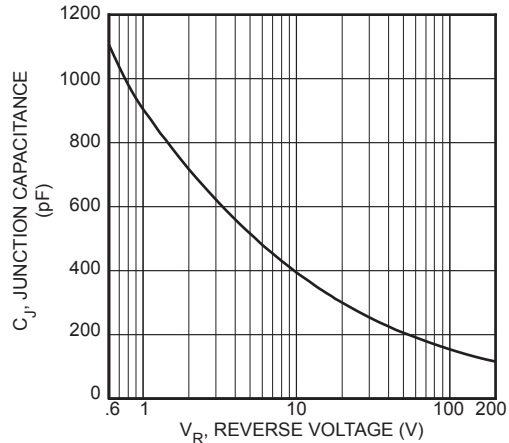


Figure 8. Junction Capacitance vs. Reverse Voltage

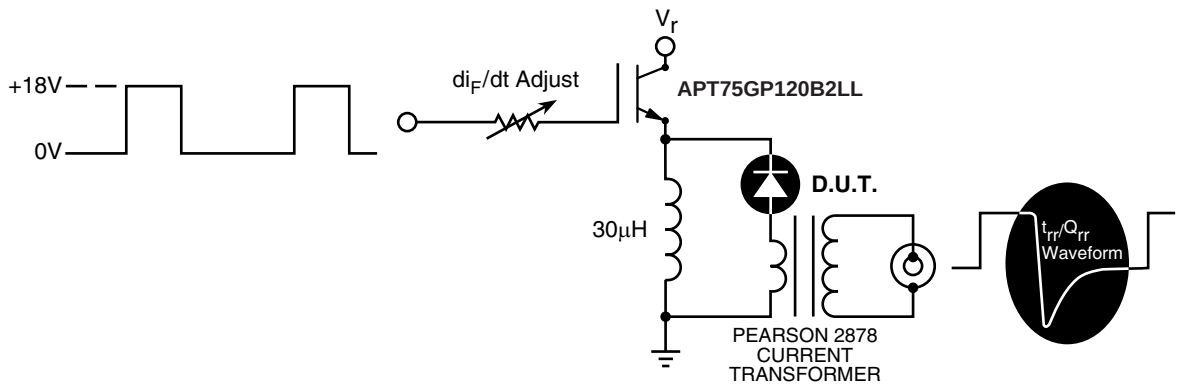


Figure 9. Diode Test Circuit

- 1 I_F - Forward Conduction Current
- 2 di_F/dt - Rate of Diode Current Change Through Zero Crossing.
- 3 I_{RRM} - Maximum Reverse Recovery Current.
- 4 t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \cdot I_{RRM}$ passes through zero.
- 5 Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr} .

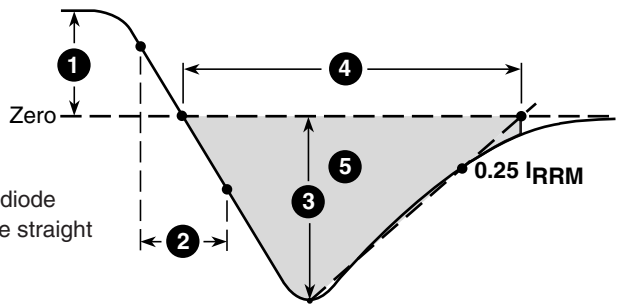
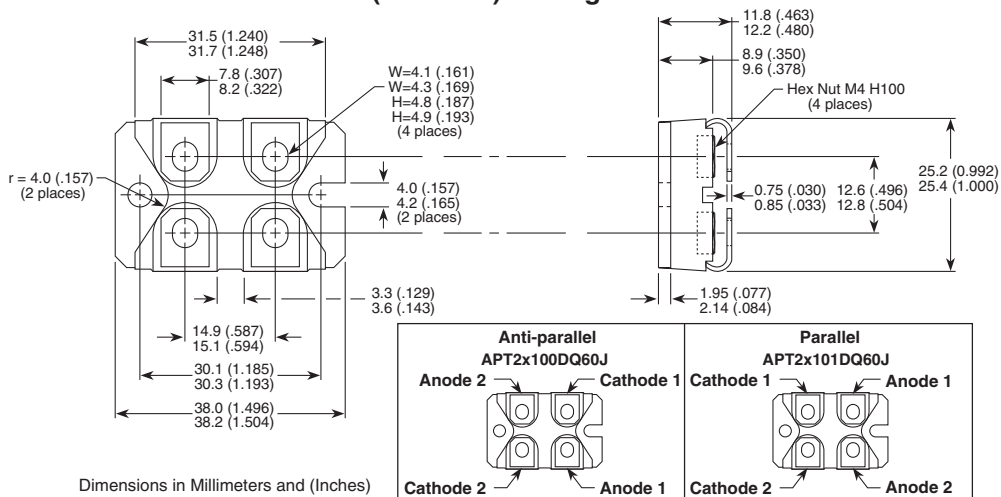
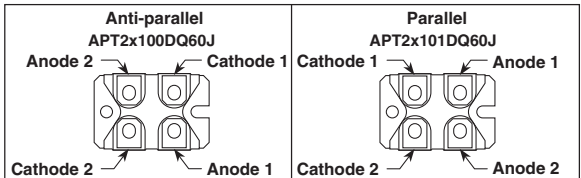


Figure 10. Diode Reverse Recovery Waveform and Definitions

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters and (Inches)



Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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